

Substrate and the manufacturing method thereof for producing a wide bandgap bi-directional switch

ABSTRACT

The invention proposes a substrate and the manufacturing method thereof for producing a bi-directional switch. This method comprises:

- transferring a first seed layer (21) made of a wide bandgap polar semiconductor material onto the front face of a carrier substrate;
- transferring a second seed layer (22) made of said wide bandgap polar semiconductor material onto the rear face of the carrier substrate.

These transfers are carried out so as to expose the first type of surface (F1) of the first seed layer (21) and the first type of surface (F1) of the second seed layer (22), with a second type of surface (F2) of the first seed layer (21) and a second type of surface (F2) of the second seed layer (22) being at the interface with the front face and the rear face of the carrier substrate, respectively.

Fig. 4